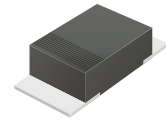


CDBMH320-G Thru. CDBMH3100-G

Reverse Voltage: 20 to 100 Volts

Forward Current: 3.0 Amp

RoHS Device

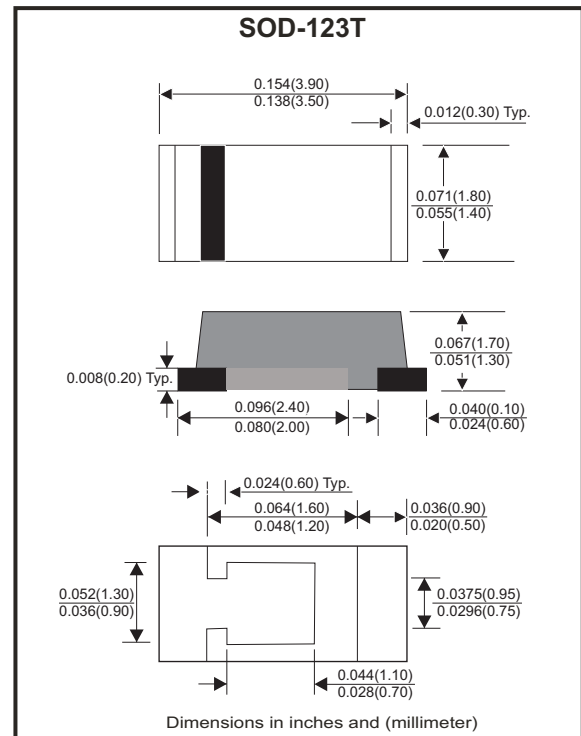


Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.
- Guardring for overvoltage protection.
- Ultra high-speed switching.
- Silicon epitaxial planar chip, metal silicon junction.
- Heat sink bottom.
- Lead-free part meets environmental standards of MIL-STD-19500/228.

Mechanical data

- Case: Molded plastic, SOD-123T/Mini SMA.
- Terminals: Solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Weight: 0.018 grams approx.



Maximum Ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	CDBMH 320-G	CDBMH 330-G	CDBMH 340-G	CDBMH 350-G	CDBMH 360-G	CDBMH 380-G	CDBMH 3100-G	Unit
Repetitive peak reverse voltage		V _{RRM}	20	30	40	50	60	80	100	V
Continuous reverse voltage		V _R	20	30	40	50	60	80	100	V
RMS voltage		V _{RMS}	14	21	28	35	42	56	70	V
Max. Forward rectified current		I _O	3.0							A
Maximum forward voltage at I _F =3.0A		V _F	0.50			0.70		0.85		V
Max. Forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I _{FSM}	80							A
Max.Reverse current	V _R =V _{RRM} T _J =25°C	I _R	0.2							mA
	V _R =V _{RRM} T _J =100°C	I _R	20							
Typ. Thermal resistance		R _{θJC}	30							°C/W
Typ. Diode Junction capacitance (Note 1)		C _J	250							pF
Operating temperature		T _J	-55 to +125			-55 to +150				°C
Storage temperature range		T _{STG}	-65 to +175							°C

Note : 1. $F=1\text{MHz}$ and applied 4V DC reverse voltage

REV:B

Rating and Characteristic Curves (CDBMH320-G Thru. CDBMH3100-G)

Fig.1 - Typical Forward Current Derating Curve

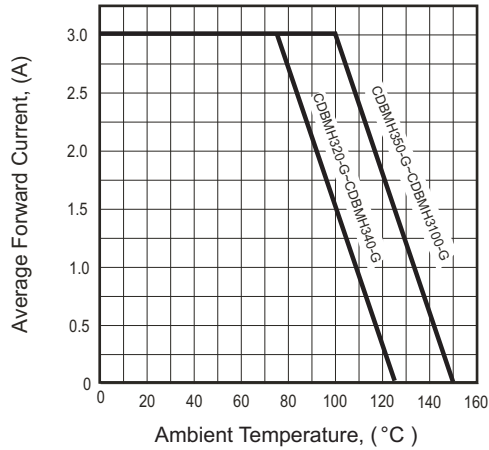


Fig.2 - Typical Forward Characteristics

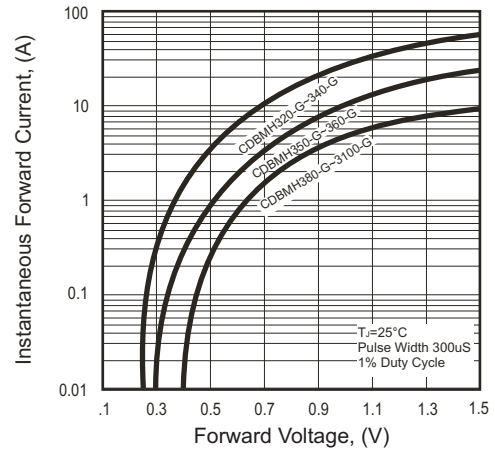


Fig.3 - Maximum Non-repetitive Forward Surge Current

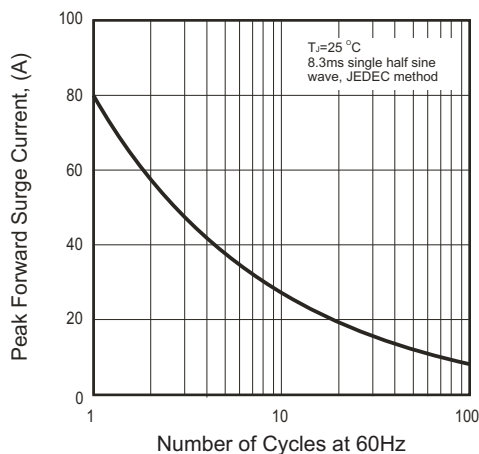


Fig.4 - Typical Junction Capacitance

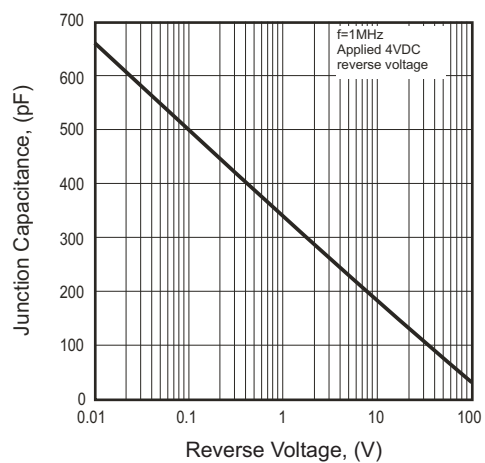
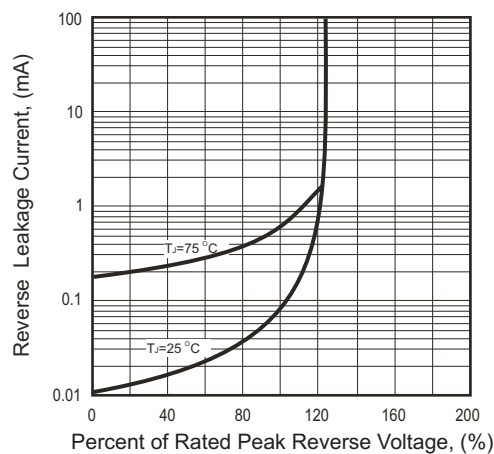
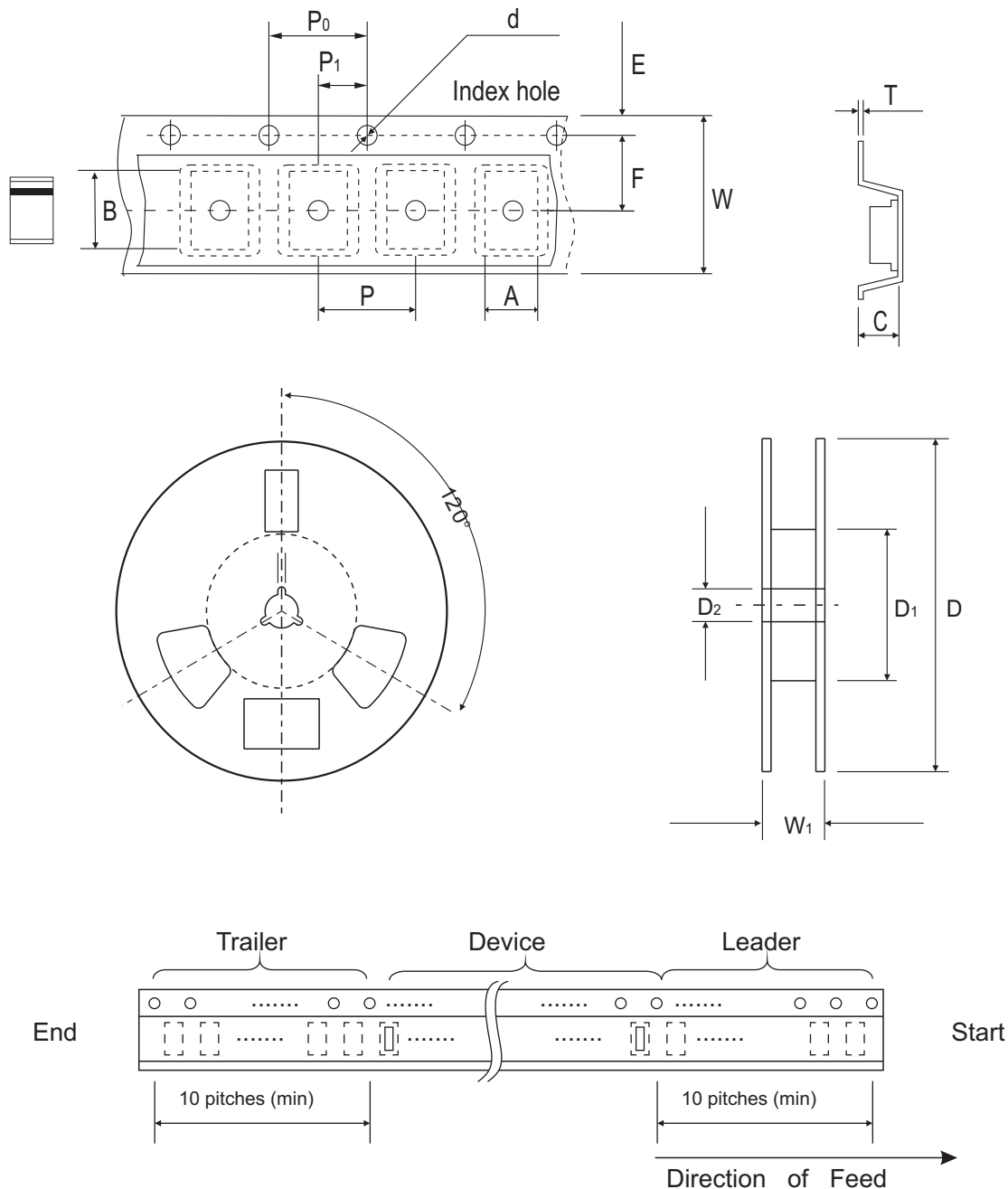


Fig.5 - Typical Reverse Characteristics



Reel Taping Specification



	SYMBOL	A	B	C	d	D	D1	D2
Mini-SMA/SOD-123T	(mm)	1.90 ± 0.10	3.90 ± 0.10	1.68 ± 0.10	1.50 ± 0.10	178 ± 2.00	62.0 MIN.	13.0 ± 0.50
	(inch)	0.075 ± 0.04	0.153 ± 0.04	0.066 ± 0.04	0.059 ± 0.004	7.00 ± 0.079	2.441 MIN.	0.512 ± 0.020

	SYMBOL	E	F	P	P0	P1	T	W	W1
Mini-SMA/SOD-123T	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.23 ± 0.10	8.00 ± 0.30	11.40 ± 1.0
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.009 ± 0.004	0.315 ± 0.012	0.449 ± 0.039

Pinning information

Pin	Simplified outline	Symbol
PIN 1 Cathode PIN 2 Anode		

Marking Code

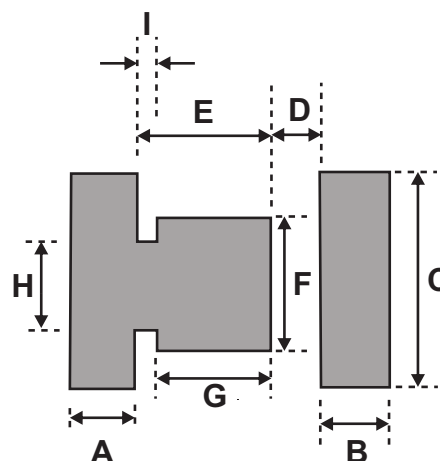
Part Number	Marking Code
CDBMH320-G	32
CDBMH330-G	33
CDBMH340-G	34
CDBMH350-G	35
CDBMH360-G	36
CDBMH380-G	38
CDBMH3100-G	310



xx / xxx = Product type marking code

Suggested PAD Layout

SIZE	Mini-SMA/SOD-123T	
	(mm)	(inch)
A	1.00	0.040
B	1.00	0.040
C	1.70	0.067
D	0.50	0.020
E	1.50	0.060
F	1.10	0.044
G	0.90	0.036
H	0.85	0.034
I	0.60	0.024



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
Mini-SMA /SOD-123T	2,500	7